

Deep Silicon Reactive Ion Etcher

- STS High Rate HRM^{ASE} (Advanced Silicon Etching) system is located in the Class-1000 cleanroom.
- It is designed to etch deep silicon structures with aspect ratios exceeding 50:1, photoresist selectivity ratios exceeding 100:1, and etch depth uniformity better than $\pm 3\%$ anisotropic.
- The ASE process achieves anisotropic etching of silicon through a series of alternating passivation and etch steps based on the “Bosch Process”.

